VS-10ETS08FP-M3, VS-10ETS12FP-M3

Vishay Semiconductors

ROHS

HALOGEN

FREE

High Voltage, Input Rectifier Diode, 10 A



21	TO-220	FullPA	١ĸ

PRIMARY CHARACTERISTICS				
I _{F(AV)}	10 A			
V_R	800 V to 1200 V			
V _F at I _F	1.1 V			
I _{FSM}	160 A			
T _J max.	150 °C			
Package	2L TO-220 FullPAK			
Circuit configuration	Single			

FEATURES

- Very low forward voltage drop
- 150 °C max. operating junction temperature
- · Glass passivated pellet chip junction
- Designed and qualified according to JEDEC®-JESD 47
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL pending
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Input rectification
- Vishay Semiconductors switches and output rectifiers which are available in identical package outlines

DESCRIPTION

High voltage rectifiers optimized for very low forward voltage drop with moderate leakage.

These devices are intended for use in main rectification (single or three phase bridge).

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C common heatsink of 1 °C/W	12.0	16.0	А		

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	VALUES	UNITS			
I _{F(AV)}	Sinusoidal waveform	10	Α			
V _{RRM}	Range	800, 1200	V			
I _{FSM}		160	А			
V _F	10 A, T _J = 25 °C	1.1	V			
TJ		-40 to +150	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA			
VS-10ETS08FP-M3	800	900	0.5			
VS-10ETS12FP-M3	1200	1300	0.5			



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ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	I _{F(AV)}	T _C = 105 °C, 180° conduction half sine wave	10	
Maximum peak one cycle	,	10 ms sine pulse, rated V _{RRM} applied	135	А
non-repetitive surge current	I _{FSM}	10 ms sine pulse, no voltage reapplied	160	
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied	91	A ² s
Maximum i-t for fusing	1-1	10 ms sine pulse, no voltage reapplied	130	A-S
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied	1300	A²√s

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum forward voltage drop	V_{FM}	10 A, T _J = 25 °C		1.1	V
Forward slope resistance	r _t	T _{.1} = 150 °C		20	$m\Omega$
Threshold voltage	V _{F(TO)}	1 J = 150 C		0.82	V
Maximum reverse leakage current	I _{RM}	T _J = 25 °C	V - Potod V	0.05	mA
waxiinuiii reveise leakage current		T _J = 150 °C	V _R = Rated V _{RRM}	0.50	IIIA

THERMAL - MECH	THERMAL - MECHANICAL SPECIFICATIONS				
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and stor temperature range	age	T _J , T _{Stg}		-40 to +150	°C
Maximum thermal resistant junction to case	ce,	R_{thJC}	DC operation	2.5	
Maximum thermal resistant junction to ambient	ce,	R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
minimum				6 (5)	kgf ⋅ cm
Mounting torque —	maximum			12 (10)	(lbf · in)
Marking device			Coop obulo 2L TO 220 EullPAK	10ETS08FP	
			Case style 2L TO-220 FullPAK		10ETS12FP



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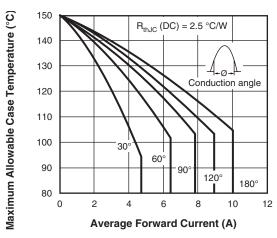


Fig. 1 - Current Rating Characteristics

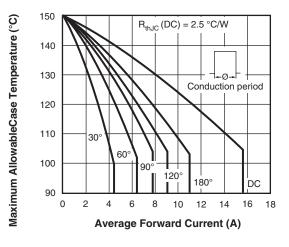


Fig. 2 - Current Rating Characteristics

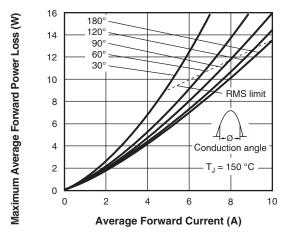


Fig. 3 - Forward Power Loss Characteristics

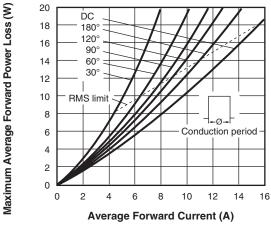


Fig. 4 - Forward Power Loss Characteristics

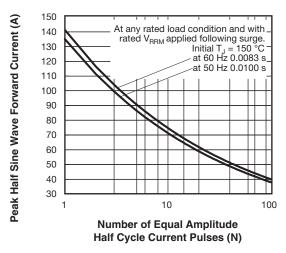


Fig. 5 - Maximum Non-Repetitive Surge Current

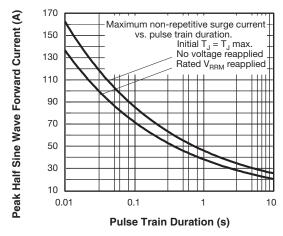


Fig. 6 - Maximum Non-Repetitive Surge Current

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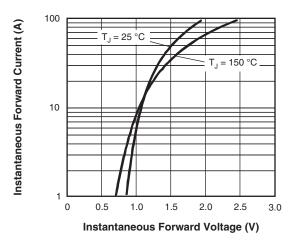


Fig. 7 - Forward Voltage Drop Characteristics

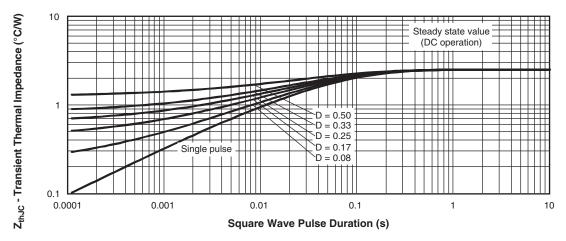


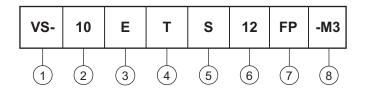
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (10 = 10 A)

Circuit configuration:

E = single diode

4 - Package:

T = TO-220

5 - Type of silicon:

S = standard recovery rectifier

6 - Voltage rating — 08 = 800 V

7 - FullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

12 = 1200 V

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-10ETS08FP-M3	50	1000	Antistatic plastic tubes		
VS-10ETS12FP-M3	50	1000	Antistatic plastic tubes		

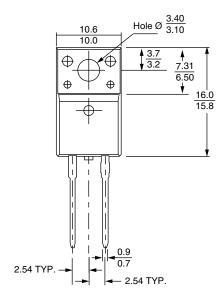
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96157</u>				
Part marking information <u>www.vishay.com/doc?95392</u>				

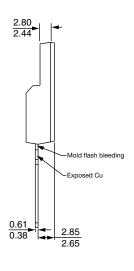


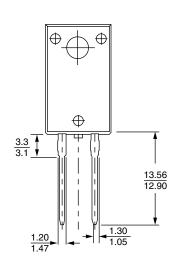
Vishay Semiconductors

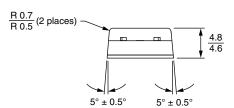
2L TO-220 FullPAK

DIMENSIONS in millimeters









Bottom view

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